ME2N7002F1KW/ME2N7002F1KW -G

Dual N-Channel 30V (D-S) MOSFET, ESD Protection

GENERAL DESCRIPTION

The ME2N7002F1KW is the Dual N-Channel logic enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology. This high density process is especially tailored to minimize on-state resistance.

FEATURES

- $R_{DS(ON)} \leqq 8\Omega @ V_{GS}=4V$
- $R_{DS(ON)} \leqq 13\Omega @ V_{GS}=2.5V$
- ESD Protection HBM 1KV
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability

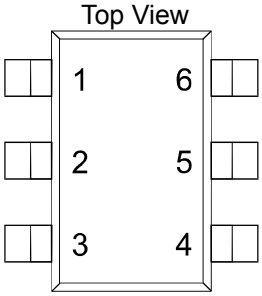
APPLICATIONS

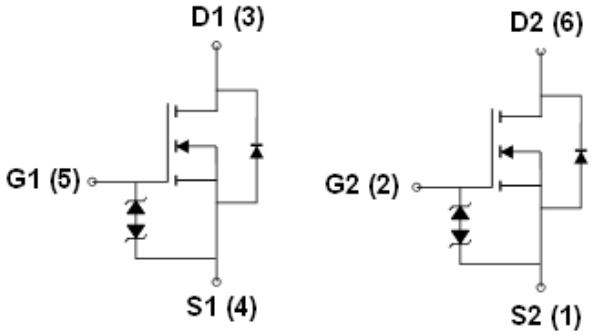
- Power Management in Note book
- DC/DC Converter
- Load Switch
- LCD Display inverter

PIN CONFIGURATION

(SOT-363)

Top View





Ordering Information: ME2N7002F1KW (Pb-free)

ME2N7002F1KW -G (Green product-Halogen free)

Absolute Maximum Ratings (T_A=25℃ Unless Otherwise Noted)

Parameter		Symbol	Maximum Ratings	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_A=25℃	I_D	0.2	A
	T_A=70℃		0.1	
Pulsed Drain Current		I_{DM}	0.6	A
Maximum Power Dissipation	T_A=25℃	P_D	0.3	W
	T_A=70℃		0.2	
Storage Temperature Range		T_{stg}	-55 to 150	℃
Thermal Resistance-Junction to Ambient*		$R_{\theta JA}$	415	℃/W

*The device mounted on 1in^2 FR4 board with 2 oz copper

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Electrical Characteristics (T_A=25℃ Unless Otherwise Specified)

Symbol	Parameter	Limit	Min	Typ	Max	Unit
STATIC						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	30			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	0.8		1.5	V
I_{GSS}	Gate Leakage Current	V_{DS}=0V, V_{GS}=±20V			±10	μA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V, V_{GS}=0V			1	μA
$R_{DS(ON)}$	Drain-Source On-Resistance[a]	V_{GS}=4V, I_D=10mA		5	8	Ω
		V_{GS}=2.5V, I_D=1mA		7	13	
V_{SD}	Diode Forward Voltage	I_S=200mA, V_{GS}=0V			1.2	V
DYNAMIC						
Qg	Total Gate Charge	V_{DS}=25V, V_{GS}=10V, I_D=0.22A		4.9		nC
Qgs	Gate-Source Charge			2.1		
Qgd	Gate-Drain Charge			0.6		
Ciss	Input Capacitance	V_{DS}=25V, V_{GS}=0V, f=1MHZ		21		pf
Coss	Output Capacitance			10		
Crss	Reverse Transfer Capacitance			2		
$t_{d(on)}$	Turn-On Delay Time	V_{DD}=5V, R_L =500Ω, V_{GEN}=5V,R_G=10Ω		10.1		ns
t_r	Turn-On Rise Time			7.3		
$t_{d(off)}$	Turn-Off Delay Time			31.3		
t_f	Turn-Off Fall Time			28.2		

Notes: a. Pulse test: pulse width≦ 300us, duty cycle≦ 2%, Guaranteed by design, not subject to production testing.

b. Matsuki Electric/ Force mos reserves the right to improve product design, functions and reliability without notice.

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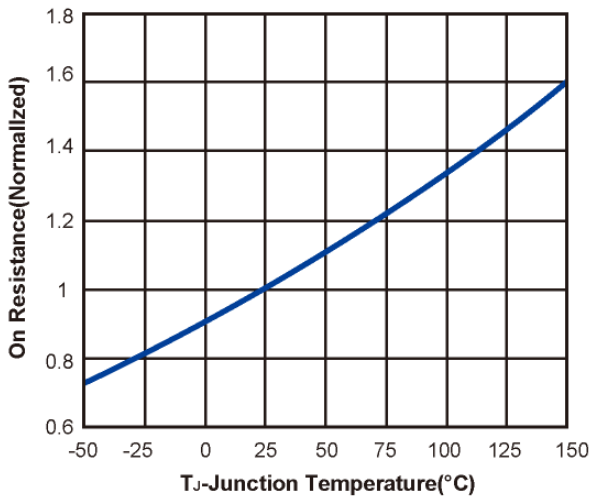
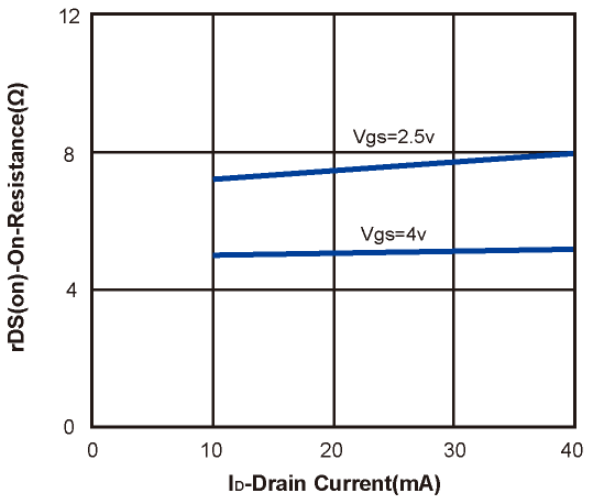
Typical Characteristics (T_J =25℃ Noted)

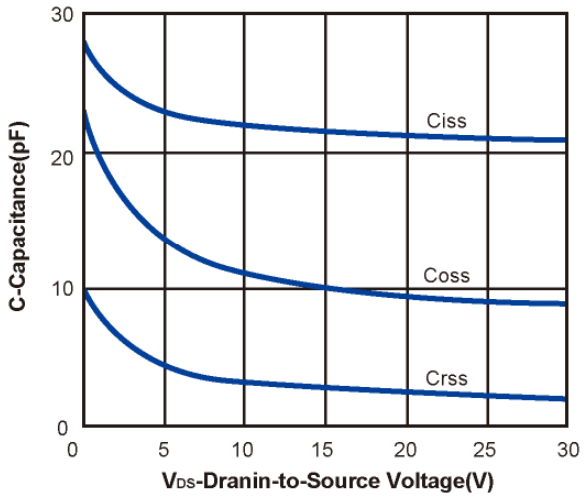
On Resistance vs. Junction Temperature



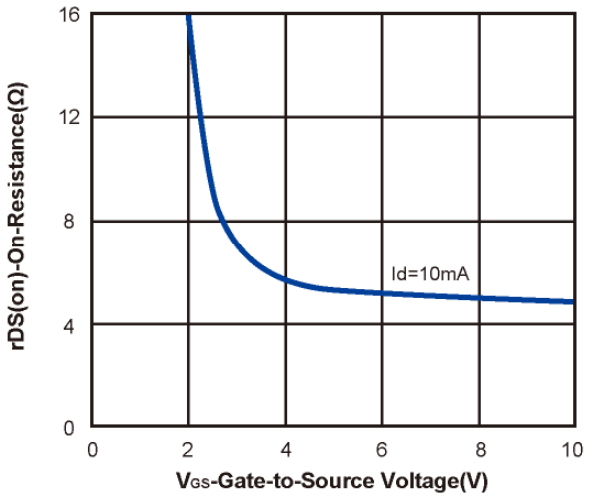
On Resistance vs. Drain Current



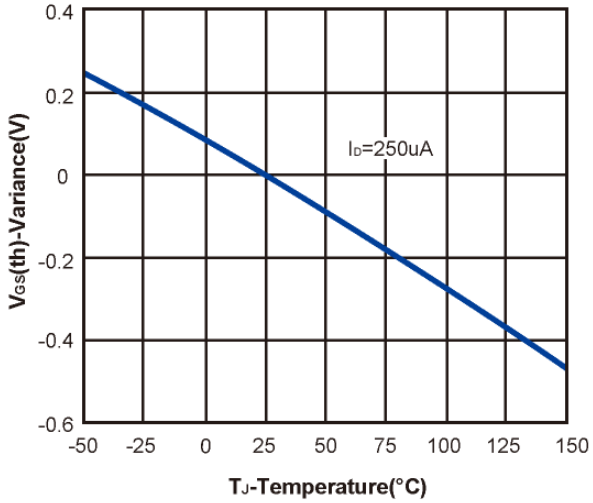
Capacitance



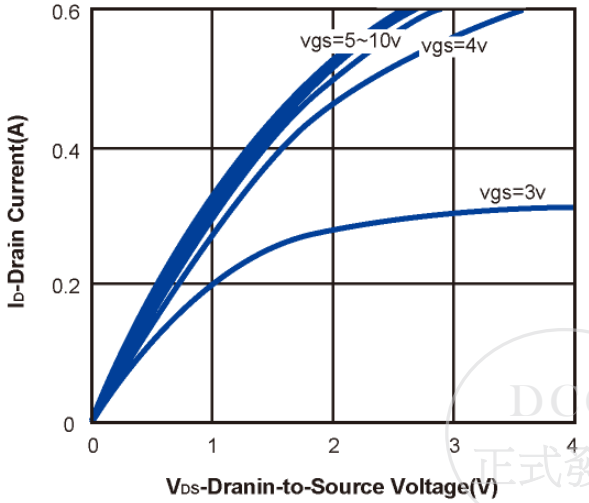
On Resistance vs. Gate-to-Source Voltage



Threshold Voltage



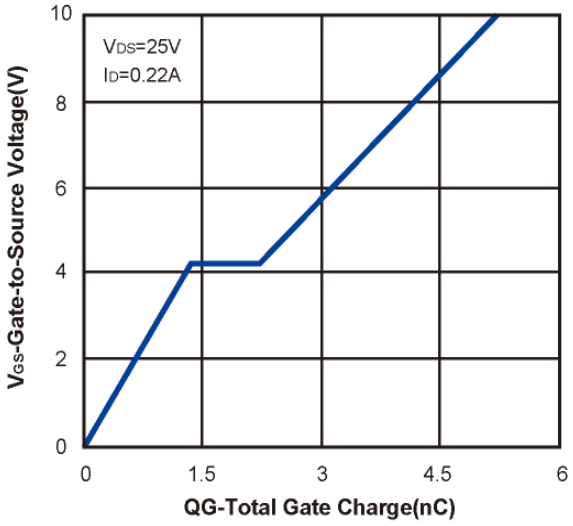
On-Region Characteristics



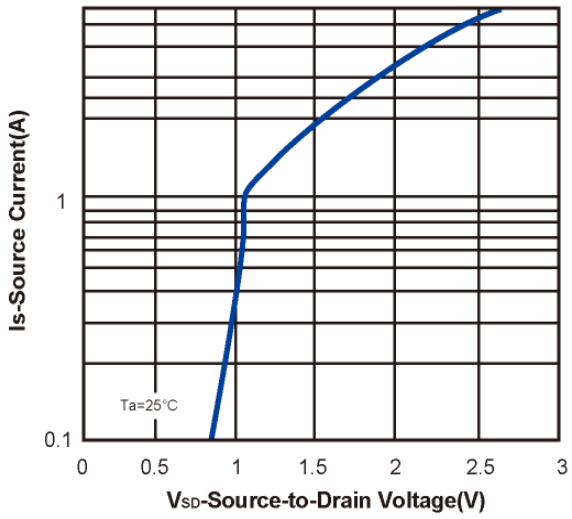
Dual N-Channel 30V (D-S) MOSFET, ESD Protection

Typical Characteristics (T_J =25℃ Noted)

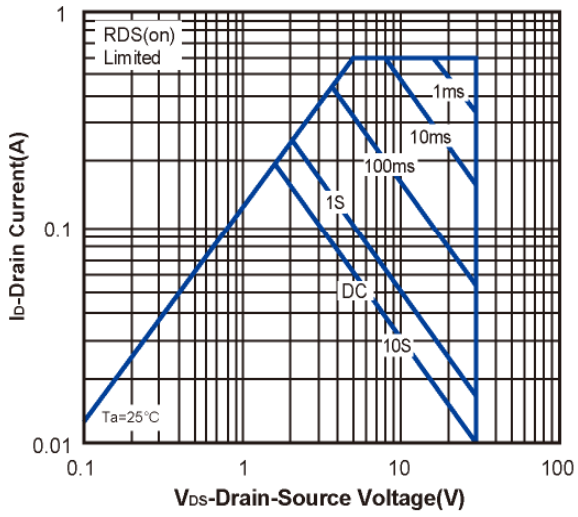
Gate Charge



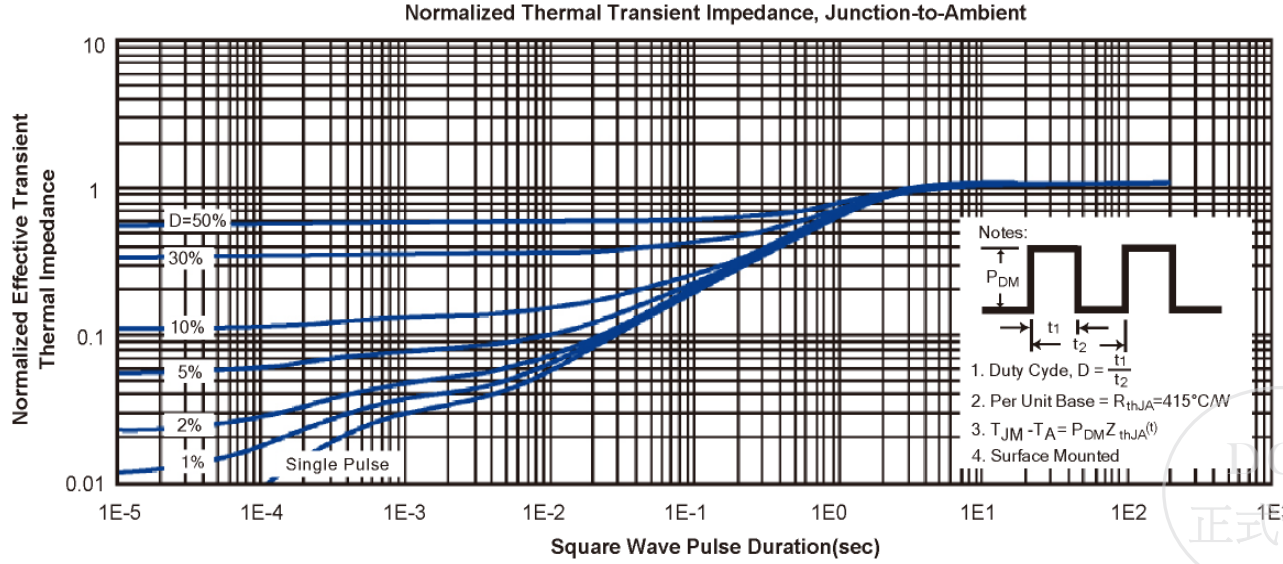
Body-diode characteristics



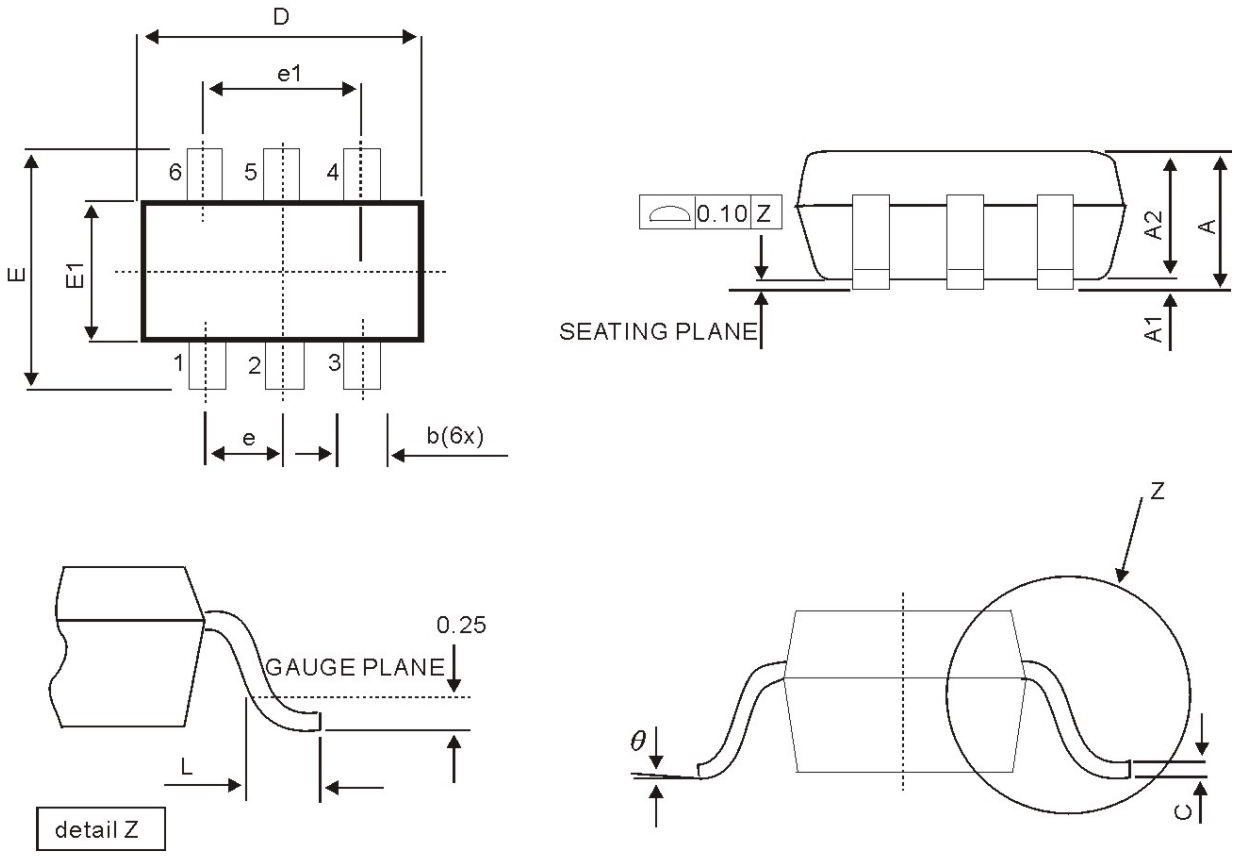
Maximum Forward Biased Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



SOT-363 Package Outline



SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A		1.10		0.043
A1	0.00	0.10	0.00	0.004
A2	0.70	1.00	0.028	0.039
b	0.15	0.30	0.006	0.012
c	0.08	0.22	0.003	0.009
D	1.80	2.15	0.073	0.085
E	1.80	2.40	0.071	0.094
E1	1.10	1.40	0.060	0.066
e	0.65 BSC		0.026 BSC	
e1	1.30 BS C		0.051 BSC	
L	0.26	0.46	0.043	0.055
θ	0°	8°	0°	8°